



# FDP8D5N10C / FDPF8D5N10C

## N-Channel Shielded Gate PowerTrench® MOSFET

100 V, 76 A, 8.5 mΩ

### Features

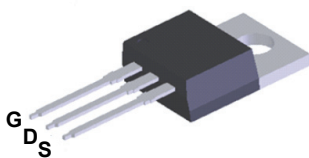
- Max  $r_{DS(on)}$  = 8.5 mΩ at  $V_{GS}$  = 10 V,  $I_D$  = 76 A
- Extremely Low Reverse Recovery Charge,  $Q_{rr}$
- 100% UIL Tested
- RoHS Compliant

### General Description

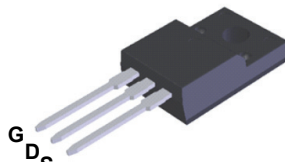
This N-Channel MV MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

### Applications

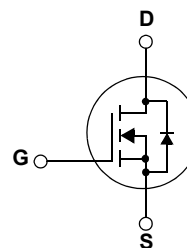
- Synchronous Rectification for ATX / Server / Telecom PSU
- Motor drives and Uninterruptible Power Supplies
- Micro Solar Inverter



TO-220



TO-220F



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol         | Parameter                                                   | Ratings     |             | Units |
|----------------|-------------------------------------------------------------|-------------|-------------|-------|
|                |                                                             | FDP8D5N10C  | FDPF8D5N10C |       |
| $V_{DS}$       | Drain to Source Voltage                                     | 100         | 100         | V     |
| $V_{GS}$       | Gate to Source Voltage                                      | ±20         | ±20         | V     |
| $I_D$          | Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note 3) | 76          | 76*         | A     |
|                | -Continuous $T_C = 100^\circ\text{C}$ (Note 3)              | 54          | 54*         |       |
|                | -Pulsed (Note 1)                                            | 304         | 304*        |       |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 2)                      | 181         |             | mJ    |
| $P_D$          | Power Dissipation $T_C = 25^\circ\text{C}$                  | 107         | 35          | W     |
|                | Power Dissipation $T_A = 25^\circ\text{C}$                  | 2.4         | 2.4         |       |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range            | -55 to +175 | -55 to +175 | °C    |

\* Drain current limited by maximum junction temperature.

### Thermal Characteristics

| Symbol          | Parameter                               | FDP8D5N10C | FDPF8D5N10C | Units |
|-----------------|-----------------------------------------|------------|-------------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 1.4        | 4.2         | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 62.5       | 62.5        |       |

### Package Marking and Ordering Information

| Device Marking | Device      | Package | Reel Size | Tape Width | Quantity |
|----------------|-------------|---------|-----------|------------|----------|
| FDP8D5N10C     | FDP8D5N10C  | TO-220  | -         | -          | 50 units |
| FDPF8D5N10C    | FDPF8D5N10C | TO-220F | -         | -          | 50 units |

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|-------|

**Off Characteristics**

|                                      |                                           |                                                             |     |    |           |                      |
|--------------------------------------|-------------------------------------------|-------------------------------------------------------------|-----|----|-----------|----------------------|
| $BV_{DSS}$                           | Drain to Source Breakdown Voltage         | $I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$           | 100 |    |           | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$ |     | 57 |           | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 80\ \text{V}$ , $V_{GS} = 0\ \text{V}$            |     |    | 1         | $\mu\text{A}$        |
|                                      |                                           | $V_{DS} = 80\ \text{V}$ , $T_J = 150^\circ\text{C}$         |     |    | 500       | $\mu\text{A}$        |
| $I_{GSS}$                            | Gate to Source Leakage Current            | $V_{GS} = \pm 20\ \text{V}$ , $V_{DS} = 0\ \text{V}$        |     |    | $\pm 100$ | nA                   |

**On Characteristics**

|              |                                      |                                                |     |     |     |            |
|--------------|--------------------------------------|------------------------------------------------|-----|-----|-----|------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage     | $V_{GS} = V_{DS}$ , $I_D = 130\ \mu\text{A}$   | 2.0 | 3.0 | 4.0 | V          |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\ \text{V}$ , $I_D = 76\ \text{A}$ |     | 7.4 | 8.5 | m $\Omega$ |
| $g_{FS}$     | Forward Transconductance             | $V_{DS} = 5\ \text{V}$ , $I_D = 76\ \text{A}$  |     | 68  |     | S          |

**Dynamic Characteristics**

|           |                              |                                                                           |     |      |      |          |
|-----------|------------------------------|---------------------------------------------------------------------------|-----|------|------|----------|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ ,<br>$f = 1\ \text{MHz}$ |     | 1765 | 2475 | pF       |
| $C_{oss}$ | Output Capacitance           |                                                                           |     | 1010 | 1415 | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                           |     | 16   | 25   | pF       |
| $R_g$     | Gate Resistance              |                                                                           | 0.1 | 0.8  | 1.6  | $\Omega$ |

**Switching Characteristics**

|              |                               |                                                                                                     |                                                   |    |    |    |
|--------------|-------------------------------|-----------------------------------------------------------------------------------------------------|---------------------------------------------------|----|----|----|
| $t_{d(on)}$  | Turn-On Delay Time            | $V_{DD} = 50\ \text{V}$ , $I_D = 76\ \text{A}$ ,<br>$V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$ |                                                   | 12 | 22 | ns |
| $t_r$        | Rise Time                     |                                                                                                     |                                                   | 11 | 20 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time           |                                                                                                     |                                                   | 18 | 28 | ns |
| $t_f$        | Fall Time                     |                                                                                                     |                                                   | 4  | 10 | ns |
| $Q_g$        | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ to $10\ \text{V}$                                                            | $V_{DD} = 50\ \text{V}$ ,<br>$I_D = 76\ \text{A}$ | 25 | 34 | nC |
| $Q_{gs}$     | Gate to Source Gate Charge    |                                                                                                     |                                                   | 9  |    | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge |                                                                                                     |                                                   | 5  |    | nC |
| $Q_{oss}$    | Output Charge                 | $V_{DD} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$                                                    |                                                   | 68 |    | nC |

**Drain-Source Diode Characteristic**

|                 |                                                          |                                                                                                         |   |     |     |    |
|-----------------|----------------------------------------------------------|---------------------------------------------------------------------------------------------------------|---|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain to Source Diode Forward Current |                                                                                                         | - | -   | 76  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain to Source Diode Forward Current     |                                                                                                         | - | -   | 304 | A  |
| V <sub>SD</sub> | Source to Drain Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 76 A                                                            |   | 1.0 | 1.3 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                    | V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 50 V, I <sub>F</sub> = 76 A,<br>dI <sub>F</sub> /dt = 100 A/μs |   | 58  | 92  | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                                  |                                                                                                         |   | 53  | 85  | nC |
| t <sub>rr</sub> | Reverse Recovery Time                                    | V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 50 V, I <sub>F</sub> = 76 A,<br>dI <sub>F</sub> /dt = 300 A/μs |   | 51  | 81  | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                                  |                                                                                                         |   | 141 | 226 | nC |

## Notes:

1. Pulsed  $I_D$  please refer to Figure 11 & Figure 12 "Forward Bias Safe Operating Area" for more details.
2.  $E_{AS}$  of 181 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 3\ \text{mH}$ ,  $I_{AS} = 11\ \text{A}$ ,  $V_{DD} = 100\ \text{V}$ ,  $V_{GS} = 10\ \text{V}$ . 100% test at  $L = 0.3\ \text{mH}$ ,  $I_{AS} = 25\ \text{A}$ .
3. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

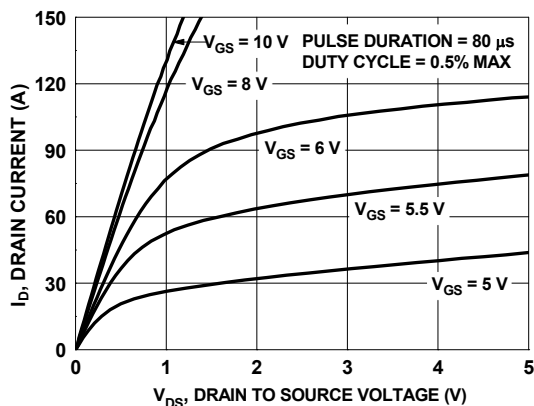


Figure 1. On Region Characteristics

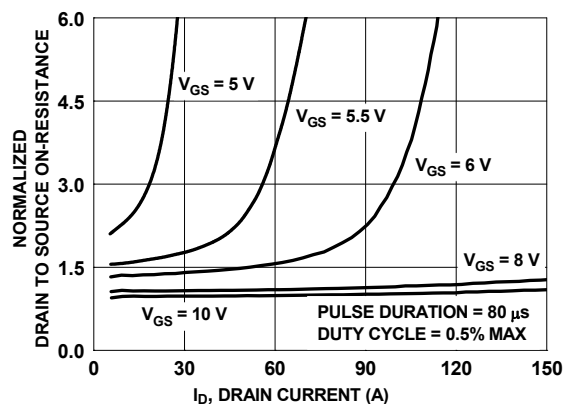


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

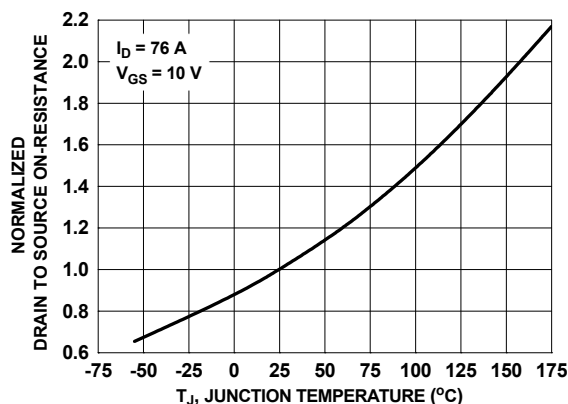


Figure 3. Normalized On Resistance vs. Junction Temperature

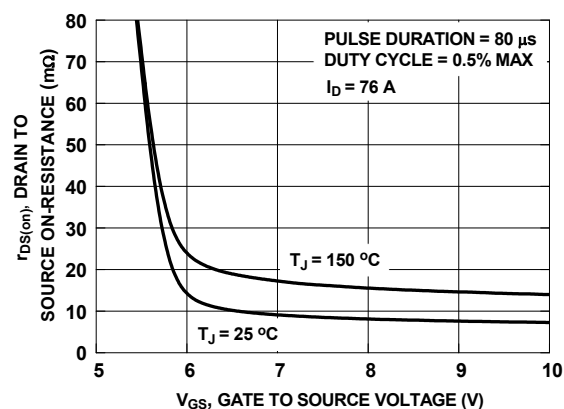


Figure 4. On-Resistance vs. Gate to Source Voltage

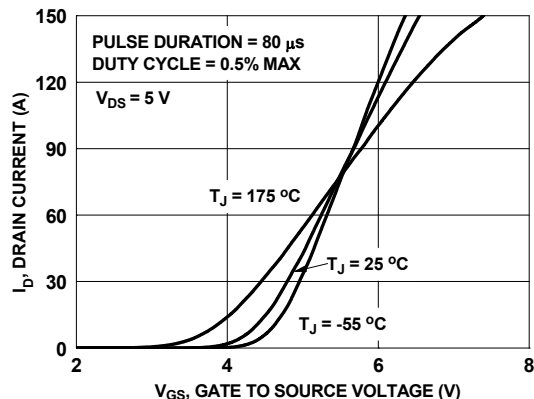


Figure 5. Transfer Characteristics

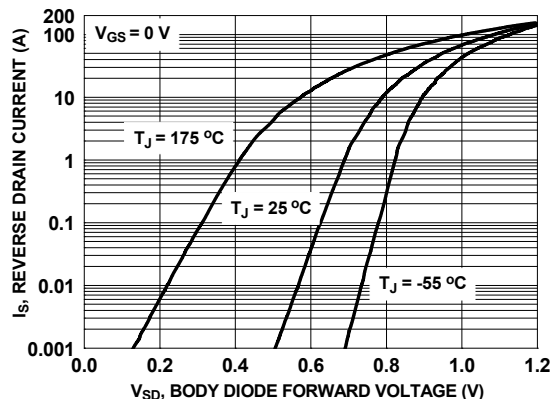


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

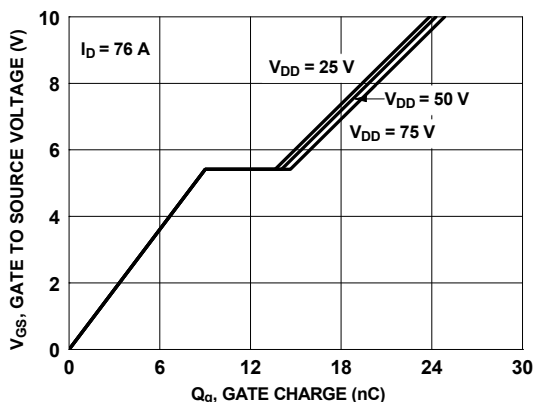


Figure 7. Gate Charge Characteristics

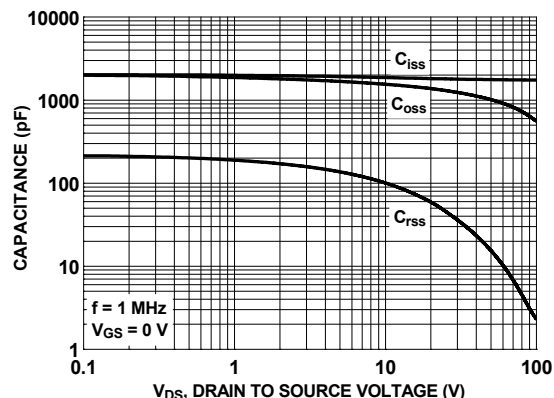


Figure 8. Capacitance vs. Drain to Source Voltage

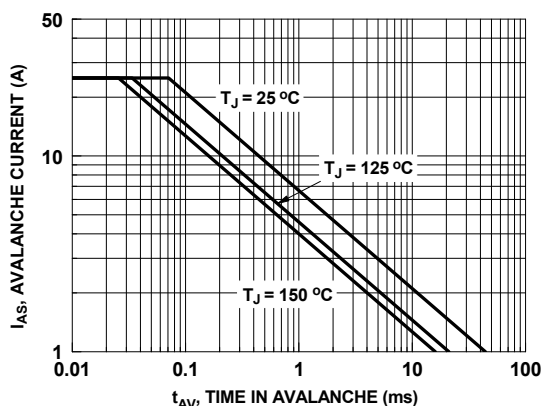


Figure 9. Unclamped Inductive Switching Capability

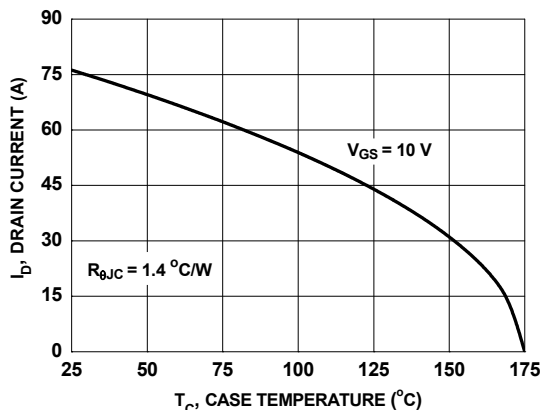


Figure 10. Maximum Continuous Drain Current vs. Case Temperature for FDP8D5N10C

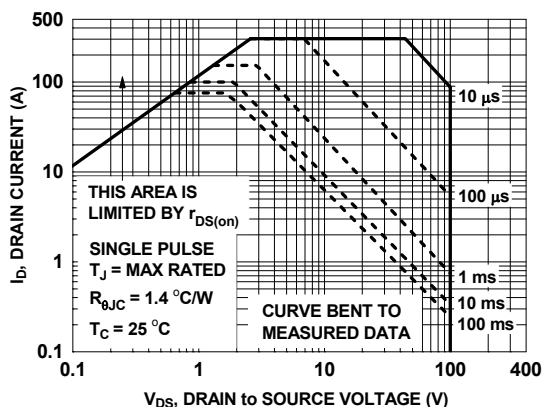


Figure 11. Forward Bias Safe Operating Area for FDP8D5N10C

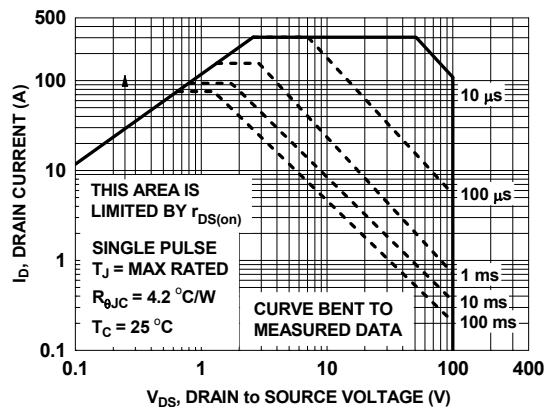


Figure 12. Forward Bias Safe Operating Area for FDPF8D5N10C

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

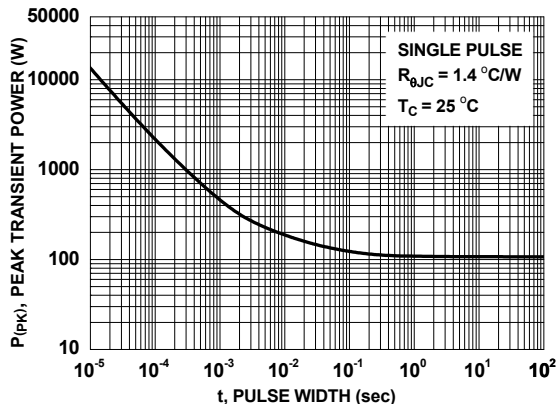


Figure 13. Single Pulse Maximum Power Dissipation for FDP8D5N10C

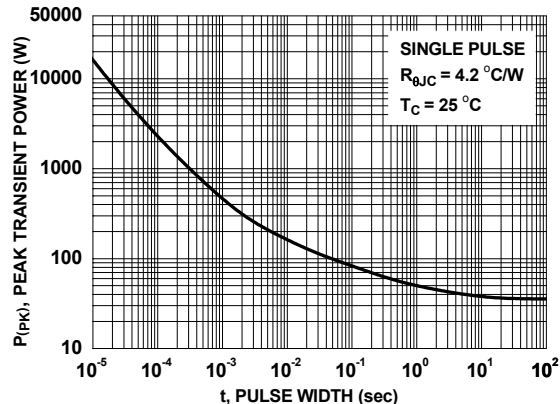


Figure 14. Single Pulse Maximum Power Dissipation for FDPF8D5N10C

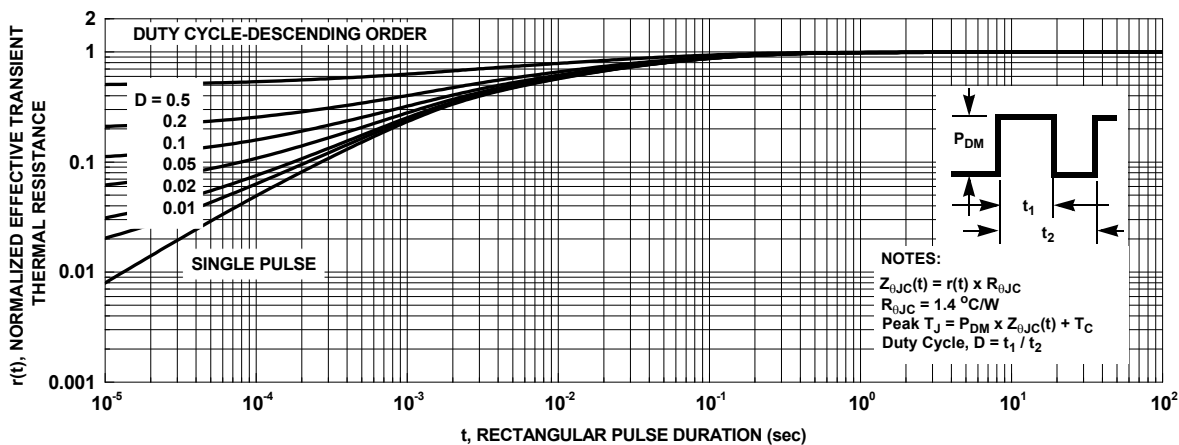


Figure 15. Junction-to-Case Transient Thermal Response Curve for FDP2D3N10C

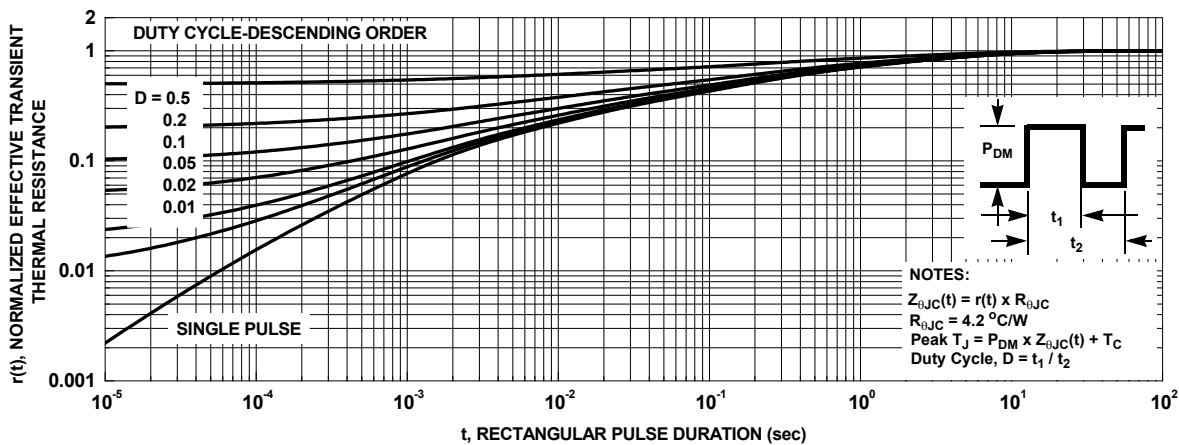


Figure 16. Junction-to-Case Transient Thermal Response Curve for FDPF2D3N10C



